

## Electronic Patent Application Fee Transmittal

<b>Application Number:</b>	10689506			
<b>Filing Date:</b>	20-Oct-2003			
<b>Title of Invention:</b>	High performance stress-enhanced MOSFETs using Si:C and SiGe epitaxial source/drain and method of manufacture			
<b>First Named Inventor:</b>	Huajie Chen			
<b>Filer:</b>	Andrew Michael Calderon/Ramon Linsangan			
<b>Attorney Docket Number:</b>	FIS920030241US1			
Filed as Large Entity				
<b>Utility      Filing Fees</b>				
<b>Description</b>	<b>Fee Code</b>	<b>Quantity</b>	<b>Amount</b>	<b>Sub-Total in USD(\$)</b>
<b>Basic Filing:</b>				
<b>Pages:</b>				
<b>Claims:</b>				
<b>Miscellaneous-Filing:</b>				
<b>Petition:</b>				
<b>Patent-Appeals-and-Interference:</b>				
Post-Allowance-and-Post-Issuance:				
<b>Extension-of-Time:</b>				

Description	Fee Code	Quantity	Amount	Sub-Total in USD(\$)
Miscellaneous:				
Submission- Information Disclosure Stmt	1806	1	180	180
Total in USD (\$)				180